- Low r<sub>DS(on)</sub> . . . 5 Ω Typical
- Avalanche Energy . . . 30 mJ
- Eight Power DMOS-Transistor Outputs of 150-mA Continuous Current
- 500-mA Typical Current-Limiting Capability
- Output Clamp Voltage . . . 50 V
- Low Power Consumption

#### description

The TPIC6B273 is a monolithic, high-voltage, medium-current, power logic octal D-type latch with DMOS-transistor outputs designed for use in systems that require relatively high load power. The device contains a built-in voltage clamp on the outputs for inductive transient protection. Power driver applications include relays, solenoids, and other medium-current or high-voltage loads.

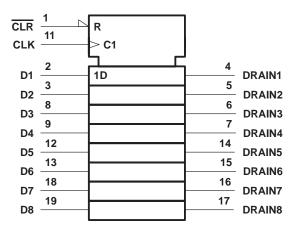
The TPIC6B273 contains eight positive-edgetriggered D-type flip-flops with a direct clear input. Each flip-flop features an open-drain power DMOS-transistor output.

When clear (CLR) is high, information at the D inputs meeting the setup time requirements is transferred to the DRAIN outputs on the positive-going edge of the clock (CLK) pulse. Clock triggering occurs at a particular voltage level and is not directly related to the transition time of the positive-going pulse. When the clock input (CLK) is at either the high or low level, the D input signal has no effect at the output. An asynchronous CLR is provided to turn all eight DMOS-transistor outputs off. When data is low for a given output, the DMOS-transistor output is off. When data is high, the DMOS-transistor output has sink-current capability.

Outputs are low-side, open-drain DMOS transistors with output ratings of 50 V and 150-mA continuous sink-current capability. Each output provides a 500-mA typical current limit at  $T_C = 25^{\circ}C$ . The current limit decreases as the junction temperature increases for additional device protection.

#### DW OR N PACKAGE (TOP VIEW) CLR [ 20 VCC D1 **∏** 19 D8 2 D2 [] 3 18 D7 DRAIN1 II 4 17 DRAIN8 DRAIN2 II 5 16 DRAIN7 DRAIN3 ☐ 6 15 DRAIN6 DRAIN4 II 7 14 DRAIN5 13 D6 D3 🛮 8 D4 🛮 9 12 D5 GND 10 11 CLK

# logic symbol†



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Standard 91-1984 and IEC Publication 617-12.

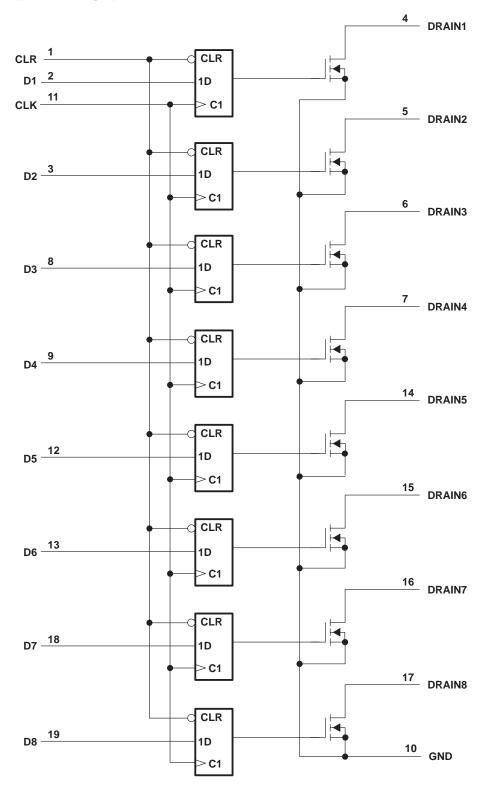
# FUNCTION TABLE (each channel)

	INPUTS		OUTPUT
CLR	CLK	D	DRAIN
L	Χ	Χ	Н
Н	$\uparrow$	Н	L
Н	$\uparrow$	L	Н
Н	L	X	Latched

H = high level, L = low level, X = irrelevant

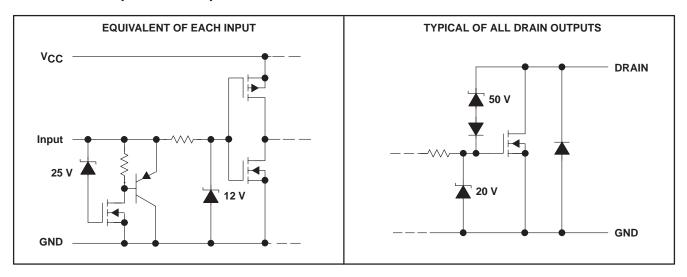
The TPIC6B273 is characterized for operation over the operating case temperature range of -40°C to 125°C.

# logic diagram (positive logic)





#### schematic of inputs and outputs



# absolute maximum ratings over recommended operating case temperature range (unless otherwise noted) $\dagger$

Logic supply voltage, V <sub>CC</sub> (see Note 1)	
Power DMOS drain-to-source voltage, V <sub>DS</sub> (see Note 2)	
Continuous source-to-drain diode anode current	
Pulsed source-to-drain diode anode current (see Note 3)	1 A
Pulsed drain current, each output, all outputs on, I <sub>D</sub> , T <sub>C</sub> = 25°C (see Note 3)	500 mA
Continuous drain current, each output, all outputs on, $I_D$ , $T_C = 25^{\circ}C$	150 mA
Peak drain current single output, I <sub>DM</sub> ,T <sub>C</sub> = 25°C (see Note 3)	500 mA
Single-pulse avalanche energy, E <sub>AS</sub> (see Figure 4)	30 mJ
Avalanche current, I <sub>AS</sub> (see Note 4)	500 mA
Continuous total dissipation	See Dissipation Rating Table
Operating virtual junction temperature range, T <sub>J</sub>	–40°C to 150°C
Operating case temperature range, T <sub>C</sub>	–40°C to 125°C
Storage temperature range	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	260°C

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values are with respect to GND.
  - 2. Each power DMOS source is internally connected to GND.
  - 3. Pulse duration  $\leq$  100  $\mu$ s and duty cycle  $\leq$  2%.
  - 4. DRAIN supply voltage = 15 V, starting junction temperature (TJS) = 25°C, L = 200 mH, IAS = 0.5 A (see Figure 4).

#### **DISSIPATION RATING TABLE**

PACKAGE	$T_C \le 25^{\circ}C$ POWER RATING	DERATING FACTOR ABOVE T <sub>C</sub> = 25°C	T <sub>C</sub> = 125°C POWER RATING
DW	1389 mW	11.1 mW/°C	278 mW
N	1050 mW	10.5 mW/°C	263 mW



SLIS031 - APRIL 1994 - REVISED JULY 1995

## recommended operating conditions

	MIN	MAX	UNIT
Logic supply voltage, V <sub>CC</sub>	4.5	5.5	V
High-level input voltage, VIH	0.85 V <sub>CC</sub>		V
Low-level input voltage, V <sub>IL</sub>		0.15 V <sub>CC</sub>	V
Pulsed drain output current, T <sub>C</sub> = 25°C, V <sub>CC</sub> = 5 V (see Notes 3 and 5)	-500	500	mA
Setup time, D high before CLK↑, t <sub>SU</sub> (see Figure 2)	20		ns
Hold time, D high after CLK↑, th (see Figure 2)	20		ns
Pulse duration, t <sub>W</sub> (see Figure 2)	40		ns
Operating case temperature, T <sub>C</sub>	-40	125	°C

# electrical characteristics, $V_{CC} = 5 \text{ V}$ , $T_{C} = 25^{\circ}\text{C}$ (unless otherwise noted)

	PARAMETER		TEST CONDITIO	ONS	MIN	TYP	MAX	UNIT
V(BR)DSX	Drain-to-source breakdown voltage	I <sub>D</sub> = 1 mA			50			٧
V <sub>SD</sub>	Source-to-drain diode forward voltage	IF = 100 mA				0.85	1	V
lн	High-level input current	$V_{CC} = 5.5 \text{ V},$	$V_I = V_{CC}$				1	μΑ
I <sub>I</sub> L	Low-level input current	$V_{CC} = 5.5 \text{ V},$	V <sub>I</sub> = 0				-1	μΑ
1	Logic gupply current	V	All outputs off	All outputs off			100	
Icc	Logic supply current	V <sub>CC</sub> = 5.5 V	All outputs on		150	300	μΑ	
I <sub>N</sub>	Nominal current	VDS(on) = 0.5 V, See Notes 5, 6, a	I <sub>N</sub> = I <sub>D</sub> , and 7	T <sub>C</sub> = 85°C,		90		mA
1	Off-state drain current	$V_{DS} = 40 \text{ V},$	V <sub>CC</sub> = 5.5 V			0.1	5	
IDSX	Oil-state drain current	V <sub>DS</sub> = 40 V,	V <sub>CC</sub> = 5.5 V,	T <sub>C</sub> = 125°C		0.15	8	μΑ
		I <sub>D</sub> = 100 mA,	V <sub>CC</sub> = 4.5 V			4.2	5.7	
rDS(on)	Static drain-to-source on-state resistance	I <sub>D</sub> = 100 mA, T <sub>C</sub> = 125°C	V <sub>CC</sub> = 4.5 V,	See Notes 5 and 6 and Figures 6 and 7		6.8	9.5	Ω
		$I_D = 350 \text{ mA},$	V <sub>CC</sub> = 4.5 V	<u> </u>		5.5	8	

# switching characteristics, $V_{CC}$ = 5 V, $T_{C}$ = 25°C

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
tPLH	Propagation delay time, low-to-high-level output from CLK		150			ns	
tPHL	Propagation delay time, high-to-low-level output from CLK	$C_L = 30 \text{ pF}, \qquad I_D = 100 \text{ mA},$		90		ns	
t <sub>r</sub>	Rise time, drain output	See Figures 1, 2, and 8		200		ns	
t <sub>f</sub>	Fall time, drain output			200		ns	
ta	Reverse-recovery-current rise time	I <sub>F</sub> = 100 mA, di/dt = 20 A/μs,		100		ne	
t <sub>rr</sub>	Reverse-recovery time	See Notes 5 and 6 and Figure 3		300		ns	

NOTES: 3. Pulse duration  $\leq$  100  $\mu$ s and duty cycle  $\leq$  2%.

- 5. Technique should limit  $T_J T_C$  to  $10^{\circ}C$  maximum.
- 6. These parameters are measured with voltage-sensing contacts separate from the current-carrying contacts.
- 7. Nominal current is defined for a consistent comparison between devices from different sources. It is the current that produces a voltage drop of 0.5 V at  $T_C$  = 85°C.



#### thermal resistance

	PARAMETER	TEST CONDITIONS	MIN	MAX	UNIT		
Po II	Thermal resistance, junction-to-ambient	DW package			90	°C/W	
$R_{\theta JA}$	Thermal resistance, junction-to-ambient	N package	All 8 outputs with equal power		95	30/00	

#### PARAMETER MEASUREMENT INFORMATION

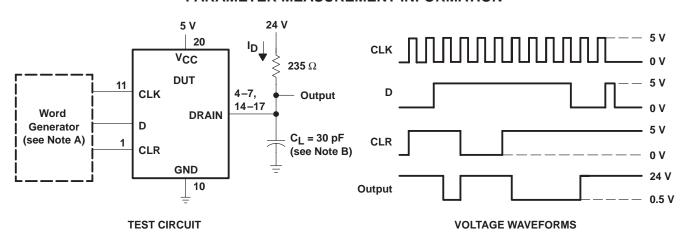


Figure 1. Resistive-Load Test Circuit and Voltage Waveforms

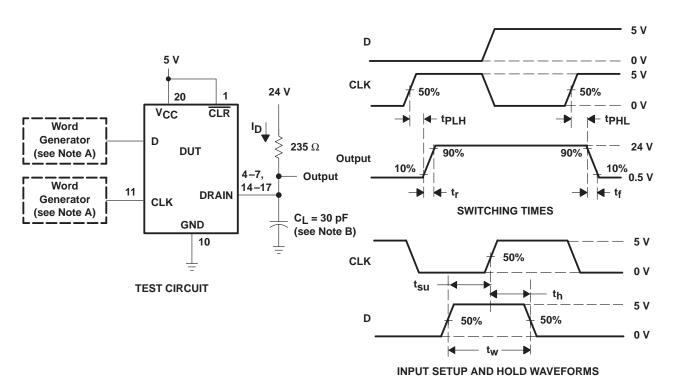


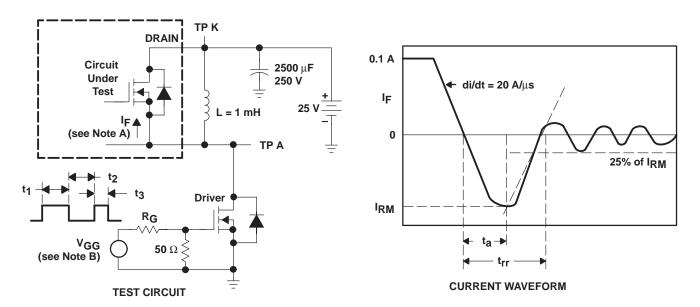
Figure 2. Test Circuit, Switching Times, and Voltage Waveforms

NOTES: A. The word generator has the following characteristics:  $t_r \le 10$  ns,  $t_f \le 10$  ns,  $t_W = 300$  ns, pulsed repetition rate (PRR) = 5 KHz,  $Z_O = 50 \ \Omega$ .

B. C<sub>L</sub> includes probe and jig capacitance.

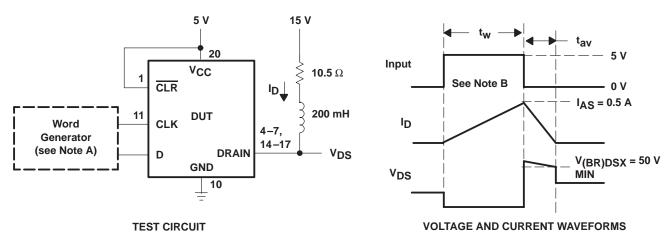


#### PARAMETER MEASUREMENT INFORMATION



- NOTES: A. The DRAIN terminal under test is connected to the TP K test point. All other terminals are connected together and connected to the TP A test point.
  - B. The  $V_{GG}$  amplitude and  $R_{G}$  are adjusted for di/dt = 20 A/ $\mu$ s. A  $V_{GG}$  double-pulse train is used to set  $I_{F}$  = 0.1 A, where  $t_{1}$  = 10  $\mu$ s,  $t_{2}$  = 7  $\mu$ s, and  $t_{3}$  = 3  $\mu$ s.

Figure 3. Reverse-Recovery-Current Test Circuit and Waveforms of Source-to-Drain Diode



- NOTES: A. The word generator has the following characteristics:  $t_r \le 10$  ns,  $t_f \le 10$  ns,  $Z_O = 50 \ \Omega$ .
  - B. Input pulse duration,  $t_W$ , is increased until peak current  $I_{AS} = 0.5$  A. Energy test is defined as  $E_{AS} = I_{AS} \times V_{(BR)DSX} \times t_{av}/2 = 30$  mJ.

Figure 4. Single-Pulse Avalanche Energy Test Circuit and Waveforms



DRAIN-TO-SOURCE ON-STATE RESISTANCE

#### TYPICAL CHARACTERISTICS

# PEAK AVALANCHE CURRENT VS TIME DURATION OF AVALANCHE 10 TC = 25°C 4 0.4 0.2 0.1 0.1 0.1 0.2 0.4 1 2 4 10

Figure 5

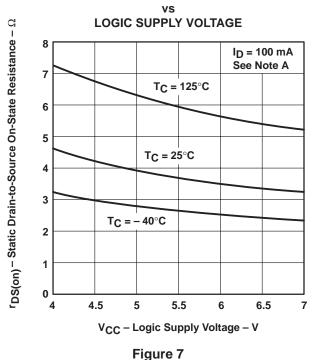
tav - Time Duration of Avalanche - ms

#### **DRAIN CURRENT** $^{ m LDS(on)}$ –Drain-to-Source On-State Resistance – $^{ m CO}$ $V_{CC} = 5 V$ See Note A 16 14 T<sub>C</sub> = 125°C 12 10 8 6 T<sub>C</sub> = 25°C $T_C = -40^{\circ}C$ 2 0 100 200 300 400 500 600 700

Figure 6

ID - Drain Current - mA

#### STATIC DRAIN-TO-SOURCE ON-STATE RESISTANCE



NOTE C: Technique should limit T<sub>J</sub> – T<sub>C</sub> to 10°C maximum.

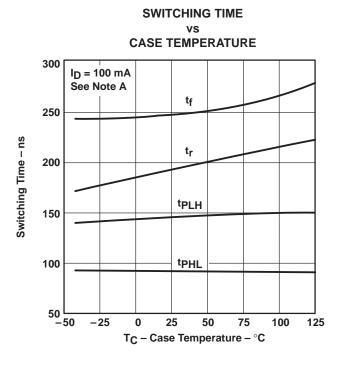


Figure 8



#### THERMAL INFORMATION

#### **MAXIMUM CONTINUOUS** DRAIN CURRENT OF EACH OUTPUT NUMBER OF OUTPUTS CONDUCTING **SIMULTANEOUSLY** 0.45 $V_{CC} = 5 V$ $I_D - Maximum Continuous Drain Current$ 0.4 0.35 0.3 of Each Output - A 0.25 T<sub>C</sub> = 25°C 0.2 0.15 T<sub>C</sub> = 100°C 0.1 T<sub>C</sub> = 125°C 0.05 0 2 3 4 5 7 8 6 N - Number of Outputs Conducting Simultaneously

Figure 9

#### **MAXIMUM PEAK DRAIN CURRENT OF EACH OUTPUT** NUMBER OF OUTPUTS CONDUCTING **SIMULTANEOUSLY** - Maximum Peak Drain Current of Each Output - A 0.5 d = 10%0.45 d = 20%0.4 0.35 d = 50%0.3 0.25 d = 80%0.2 0.15 $V_{CC} = 5 V$ $T_{C} = 25^{\circ}C$ 0.1 $d = t_W/t_{period}$ 0.05 = 1 ms/t<sub>period</sub> ۵ 3 8 N - Number of Outputs Conducting Simultaneously

Figure 10





23-Apr-2012

#### **PACKAGING INFORMATION**

Orderable Device	Status <sup>(1)</sup>	Package Type	Package Drawing	Pins	Package Qty	Eco Plan <sup>(2)</sup>	Lead/ Ball Finish	MSL Peak Temp <sup>(3)</sup>	Samples (Requires Login)
TPIC6B273DW	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273DWG4	ACTIVE	SOIC	DW	20	25	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273DWR	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273DWRG4	ACTIVE	SOIC	DW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	
TPIC6B273N	ACTIVE	PDIP	N	20	20	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type	

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

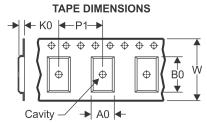
In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

# PACKAGE MATERIALS INFORMATION

www.ti.com 4-Jan-2013

## TAPE AND REEL INFORMATION





A0	
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TPIC6B273DWR	SOIC	DW	20	2000	330.0	24.4	10.8	13.3	2.7	12.0	24.0	Q1

**PACKAGE MATERIALS INFORMATION** 

www.ti.com 4-Jan-2013



#### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TPIC6B273DWR	SOIC	DW	20	2000	367.0	367.0	45.0

# N (R-PDIP-T\*\*)

# PLASTIC DUAL-IN-LINE PACKAGE

16 PINS SHOWN



NOTES:

- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- Falls within JEDEC MS-001, except 18 and 20 pin minimum body length (Dim A).
- The 20 pin end lead shoulder width is a vendor option, either half or full width.



DW (R-PDSO-G20)

## PLASTIC SMALL OUTLINE



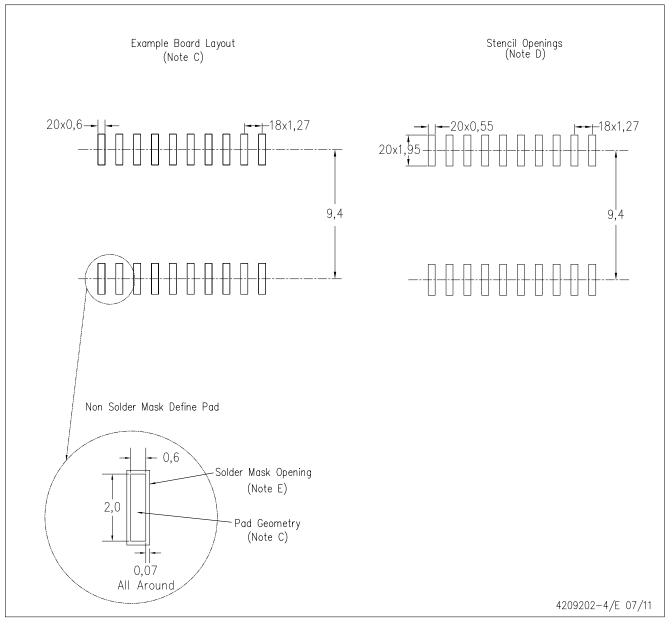
NOTES: A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M-1994.

- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
- D. Falls within JEDEC MS-013 variation AC.



DW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



NOTES:

- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Refer to IPC7351 for alternate board design.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC—7525
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



#### IMPORTANT NOTICE

Texas Instruments Incorporated and its subsidiaries (TI) reserve the right to make corrections, enhancements, improvements and other changes to its semiconductor products and services per JESD46, latest issue, and to discontinue any product or service per JESD48, latest issue. Buyers should obtain the latest relevant information before placing orders and should verify that such information is current and complete. All semiconductor products (also referred to herein as "components") are sold subject to TI's terms and conditions of sale supplied at the time of order acknowledgment.

TI warrants performance of its components to the specifications applicable at the time of sale, in accordance with the warranty in TI's terms and conditions of sale of semiconductor products. Testing and other quality control techniques are used to the extent TI deems necessary to support this warranty. Except where mandated by applicable law, testing of all parameters of each component is not necessarily performed.

TI assumes no liability for applications assistance or the design of Buyers' products. Buyers are responsible for their products and applications using TI components. To minimize the risks associated with Buyers' products and applications, Buyers should provide adequate design and operating safeguards.

TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right relating to any combination, machine, or process in which TI components or services are used. Information published by TI regarding third-party products or services does not constitute a license to use such products or services or a warranty or endorsement thereof. Use of such information may require a license from a third party under the patents or other intellectual property of the third party, or a license from TI under the patents or other intellectual property of TI.

Reproduction of significant portions of TI information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations, and notices. TI is not responsible or liable for such altered documentation. Information of third parties may be subject to additional restrictions.

Resale of TI components or services with statements different from or beyond the parameters stated by TI for that component or service voids all express and any implied warranties for the associated TI component or service and is an unfair and deceptive business practice. TI is not responsible or liable for any such statements.

Buyer acknowledges and agrees that it is solely responsible for compliance with all legal, regulatory and safety-related requirements concerning its products, and any use of TI components in its applications, notwithstanding any applications-related information or support that may be provided by TI. Buyer represents and agrees that it has all the necessary expertise to create and implement safeguards which anticipate dangerous consequences of failures, monitor failures and their consequences, lessen the likelihood of failures that might cause harm and take appropriate remedial actions. Buyer will fully indemnify TI and its representatives against any damages arising out of the use of any TI components in safety-critical applications.

In some cases, TI components may be promoted specifically to facilitate safety-related applications. With such components, TI's goal is to help enable customers to design and create their own end-product solutions that meet applicable functional safety standards and requirements. Nonetheless, such components are subject to these terms.

No TI components are authorized for use in FDA Class III (or similar life-critical medical equipment) unless authorized officers of the parties have executed a special agreement specifically governing such use.

Only those TI components which TI has specifically designated as military grade or "enhanced plastic" are designed and intended for use in military/aerospace applications or environments. Buyer acknowledges and agrees that any military or aerospace use of TI components which have *not* been so designated is solely at the Buyer's risk, and that Buyer is solely responsible for compliance with all legal and regulatory requirements in connection with such use.

TI has specifically designated certain components as meeting ISO/TS16949 requirements, mainly for automotive use. In any case of use of non-designated products, TI will not be responsible for any failure to meet ISO/TS16949.

Products Applications

Audio www.ti.com/audio Automotive and Transportation www.ti.com/automotive Communications and Telecom **Amplifiers** amplifier.ti.com www.ti.com/communications **Data Converters** dataconverter.ti.com Computers and Peripherals www.ti.com/computers **DLP® Products** www.dlp.com Consumer Electronics www.ti.com/consumer-apps

DSP **Energy and Lighting** dsp.ti.com www.ti.com/energy Clocks and Timers www.ti.com/clocks Industrial www.ti.com/industrial Interface interface.ti.com Medical www.ti.com/medical logic.ti.com Logic Security www.ti.com/security

Power Mgmt power.ti.com Space, Avionics and Defense www.ti.com/space-avionics-defense

Microcontrollers <u>microcontroller.ti.com</u> Video and Imaging <u>www.ti.com/video</u>

RFID www.ti-rfid.com

OMAP Applications Processors <a href="www.ti.com/omap">www.ti.com/omap</a> TI E2E Community <a href="e2e.ti.com">e2e.ti.com</a>

Wireless Connectivity <u>www.ti.com/wirelessconnectivity</u>